

2SC2590

Silicon NPN epitaxial planar type

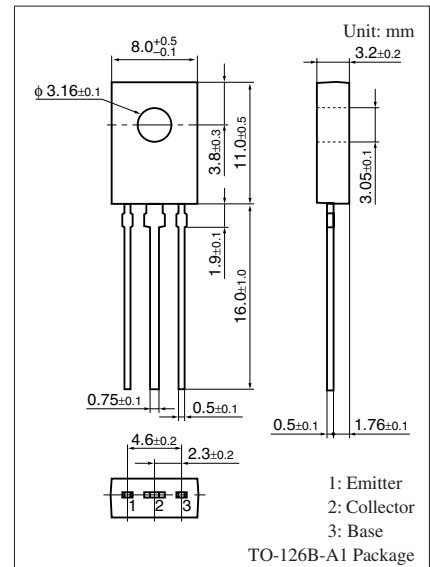
For low-frequency power amplification

■ Features

- Excellent collector current I_C characteristics of forward current transfer ratio h_{FE}
- High transition frequency f_T
- TO-126B package which requires no insulation plate for installation to the heat sink

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	120	V
Collector-emitter voltage (Base open)	V_{CEO}	120	V
Emitter-base voltage (Collector open)	V_{EBO}	5	V
Collector current	I_C	0.5	A
Peak collector current	I_{CP}	1.0	A
Collector power dissipation	P_C	1.2	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 100 \mu\text{A}, I_B = 0$	120			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu\text{A}, I_C = 0$	5			V
Forward current transfer ratio ^{*1}	h_{FE1} ^{*2}	$V_{CE} = 10 \text{ V}, I_C = 150 \text{ mA}$	90		220	—
	h_{FE2}	$V_{CE} = 5 \text{ V}, I_C = 500 \text{ mA}$	65	100		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$			1.0	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$			1.2	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		11	20	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

*2: Rank classification

Rank	Q	R
h_{FE1}	90 to 155	130 to 220

